ABSTRACT

A reflective mask blank has: a substrate; a multilayer reflective film that is provided on one surface of the substrate and reflects at least EUV light; and a back conductive film that is provided on the other surface of the substrate. The back conductive film has a layer which has a film thickness of 50 nm or more and less than 80 nm, contains tantalum (Ta), silicon (Si) and nitrogen (N), has a nitrogen content of 18 atom% or more and less than 35 atom%, and has a CSi/(CTa + CSi) of 3% or more and less than 50% when a silicon content in atom% is denoted by CSi and a tantalum content in atom% is denoted by CTa.

Figure 1